



#### 60V NPN LOW VCESAT TRANSISTOR IN PowerDI3333-8

#### **Features**

- BV<sub>CEO</sub> > 60V
- Small Form Factor Thermally Efficient Package.
   Enables Higher Density End Products
- I<sub>C</sub> = 6A high Continuous Collector Current
- I<sub>CM</sub> = 20A Peak Pulse Current
- Low Saturation Voltage V<sub>CE(sat)</sub> < 60mV @ 1A</li>
- hFE Specified Up to 10A for a High Gain Hold Up
- Complementary PNP Type: DXTP03060CFG
- Wettable Flank for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <a href="https://www.diodes.com/quality/product-definitions/">https://www.diodes.com/quality/product-definitions/</a>

#### **Mechanical Data**

- Case: PowerDI<sup>®</sup>3333-8
- Case Material: Molded Plastic. "Green" Molding Compound UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.03 grams (Approximate)

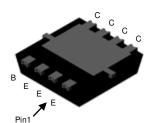
### **Applications**

- MOSFET & IGBT Gate Drivers
- · Solenoid, Relay and Actuator Drivers
- DC to DC Converters
- Motor Control

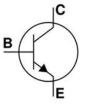
PowerDI3333-8 (SWP) (Type UX)



Top View



**Bottom View** 



Device Symbol

### **Ordering Information** (Note 4)

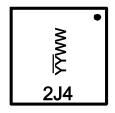
| Part Number    | Compliance | Marking | Reel Size (inches) | Tape Width (mm) | Quantity Per Reel |
|----------------|------------|---------|--------------------|-----------------|-------------------|
| DXTN03060CFG-7 | Standard   | 2J4     | 7                  | 12              | 2,000             |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# Marking Information

PowerDI3333-8 (SWP) (Type UX)



2J4 = Product Type Marking Code

\text{YYWW} = Date Code Marking

\text{YY} = Last Two Digits of Year (ex: 21 = 2021)}

WW = Week Code (01 to 53)



### **Maximum Ratings** (@TA = +25°C, unless otherwise specified.)

| Characteristic               | Symbol | Value | Unit |
|------------------------------|--------|-------|------|
| Collector-Base Voltage       | Vcво   | 100   | V    |
| Collector-Emitter Voltage    | VCEO   | 60    | V    |
| Emitter-Base Voltage         | VEBO   | 7     | V    |
| Continuous Collector Current | Ic     | 6     | Α    |
| Peak Pulse Current           | Ісм    | 20    | Α    |

# Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

| Characteristic                                 | Symbol   | Value              | Unit |      |
|--|----------|--------------------|------|------|
| Bower Dissipation                              | (Note 5) | D-                 | 1.2  | W    |
| Power Dissipation                              | (Note 6) | - P <sub>D</sub>   | 2.7  | W    |
| Thermal Posistance, Juneties to Ambient        | (Note 5) | D                  | 107  | °C/W |
| Thermal Resistance, Junction to Ambient        | (Note 6) | - R <sub>0JA</sub> | 48   | °C/W |
| Thermal Resistance, Junction to Leads (Note 7) | Rejl     | 8.5                | °C/W |      |
| Operating and Storage Temperature Range        | TJ, TSTG | -55 to +150        | °C   |      |

### ESD Ratings (Note 8)

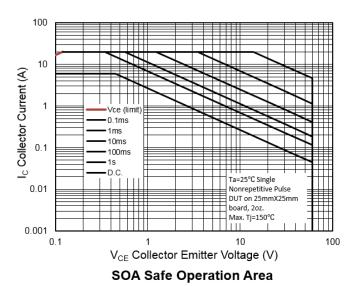
| Characteristic                             | Symbol  | Value | Unit | JEDEC Class |
|--|---------|-------|------|-------------|
| Electrostatic Discharge - Human Body Model | ESD HBM | 4,000 | ٧    | 3A          |
| Electrostatic Discharge - Machine Model    | ESD MM  | ≥ 400 | ٧    | С           |

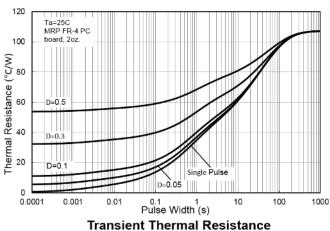
Notes:

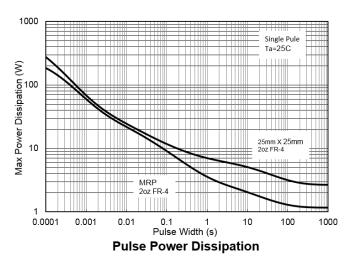
- 5. For a device mounted with the collector tab on MRP FR4-PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
- 7. Thermal resistance from junction to solder-point (at the collector tab).
- 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

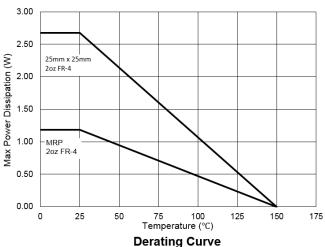


# **Thermal Characteristics and Derating Information**











# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

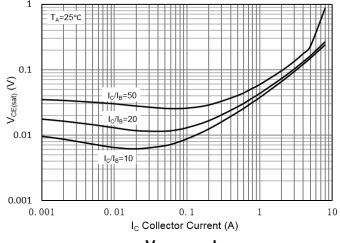
| Characteristic                                | Symbol               | Min | Тур  | Max  | Unit | Test Condition  |
|---|----------------------|-----|------|------|------|---|
| Collector-Base Breakdown Voltage              | ВУсво                | 100 | 201  | _    | V    | Ic = 100μA  |
| Collector-Emitter Breakdown Voltage (Note 9)  | BVCEO                | 60  | 78   | _    | V    | Ic = 10mA   |
| Emitter-Base Breakdown Voltage                | BV <sub>EBO</sub>    | 7   | 8.9  | _    | V    | I <sub>E</sub> = 100μA                                      |
| Collector Cut-off Current                     | Ісво                 | _   | 3    | 50   | nA   | V <sub>CB</sub> = 100V                                      |
| Conector out-on current                       | ICBO                 | _   | 0.2  | 10   | μΑ   | V <sub>CB</sub> = 100V, T <sub>A</sub> = +125°C             |
| Collector Cut-off Current                     | ICER                 | _   | 8    | 50   | nA   | V <sub>CB</sub> = 80V                                       |
| Conector out-on current                       | $R_B \le 1k\Omega$   | _   | 0.3  | 10   | μΑ   | V <sub>CB</sub> = 80V, T <sub>A</sub> = +125°C              |
| Emitter Cut-off Current                       | I <sub>EBO</sub>     | _   | 1    | 20   | nA   | V <sub>EB</sub> = 6V  |
|   |                      | 200 | 354  | _    | _    | Ic = 10mA, VcE = 2V   |
|   |                      | 200 | 357  | _    | _    | Ic = 100mA, VcE = 2V  |
| DC Current Gain (Note 9)                      | h <sub>FE</sub>      | 200 | 343  | 800  | _    | $I_C = 1A$ , $V_{CE} = 2V$                                  |
|   |                      | 200 | 325  | _    | _    | Ic = 2A, VcE = 2V   |
|   |                      | 75  | 133  |      | _    | Ic = 5A, VcE = 2V   |
|   |                      | _   | 13   | 30   | mV   | Ic = 100mA, I <sub>B</sub> = 5mA                            |
|   | VCE(sat)             | _   | 37   | 60   | mV   | I <sub>C</sub> = 1A, I <sub>B</sub> = 100mA                 |
| Collector-Emitter Saturation Voltage (Note 9) |                      | _   | 43   | 70   | mV   | Ic = 1A, I <sub>B</sub> = 50mA                              |
|   |                      | _   | 88   | 135  | mV   | Ic = 2A, I <sub>B</sub> = 50mA                              |
|   |                      | _   | 194  | 260  | mV   | I <sub>C</sub> = 6A, I <sub>B</sub> = 300mA                 |
| Base-Emitter Saturation Voltage (Note 9)      | V <sub>BE(sat)</sub> | _   | 1000 | 1100 | mV   | Ic = 6A, I <sub>B</sub> = 300mA                             |
| Base-Emitter Turn-On Voltage (Note 9)         | $V_{BE(on)}$         | _   | 930  | 1050 | mV   | Ic = 6A, VcE = 1V   |
| Input Capacitance                             | Cibo                 | _   | 509  | _    | pF   | V <sub>EB</sub> = 0.5V. f = 1MHz                            |
| Output Capacitance                            | C <sub>obo</sub>     | _   | 290  | _    | pF   | V <sub>CB</sub> = 10V. f = 1MHz                             |
| Current Gain-Bandwidth Product                | fт                   | _   | 140  | _    | MHz  | V <sub>CE</sub> = 5V, I <sub>C</sub> = 100mA,<br>f = 100MHz |
|   | tdelay               | _   | 16.5 | _    | ns   |   |
| Switching Time                                | trise                | _   | 5.8  | _    | ns   | $I_{C} = 1A, V_{CC} = 10V,$                                 |
| Switching fille                               | t <sub>storage</sub> | _   | 1273 | _    | ns   | $I_{B1} = -I_{B2} = 100 \text{mA}$                          |
|   | t <sub>fall</sub>    | _   | 27.5 | _    | ns   |   |

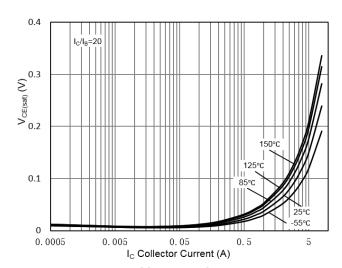
Note:

9. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.

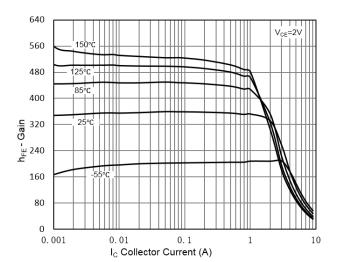


## Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

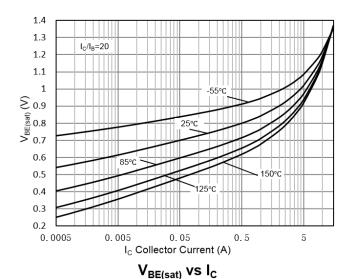




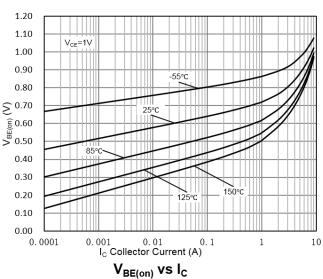


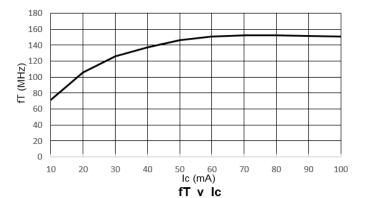


 $V_{\text{CE(sat)}} vs I_{\text{C}}$ 



 $h_{\text{FE}}$  vs  $I_{\text{C}}$ 



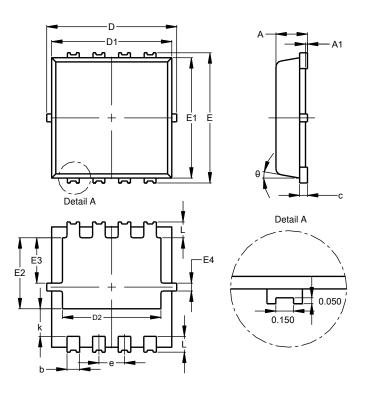




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI3333-8 (SWP) (Type UX)

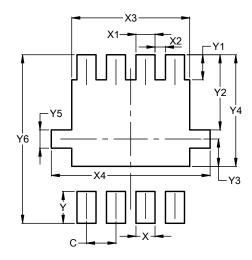


| PowerDI3333-8 (SWP)  |      |      |      |  |  |  |
|----------------------|------|------|------|--|--|--|
| (Type UX)            |      |      |      |  |  |  |
| Dim                  | Min  | Max  | Тур  |  |  |  |
| Α                    | 0.75 | 0.85 | 0.80 |  |  |  |
| <b>A</b> 1           | 0.00 | 0.05 |      |  |  |  |
| b                    | 0.25 | 0.40 | 0.32 |  |  |  |
| С                    | 0.10 | 0.25 | 0.15 |  |  |  |
| D                    | 3.20 | 3.40 | 3.30 |  |  |  |
| D1                   | 2.95 | 3.15 | 3.05 |  |  |  |
| D2                   | 2.30 | 2.70 | 2.50 |  |  |  |
| Е                    | 3.20 | 3.40 | 3.30 |  |  |  |
| E1                   | 2.95 | 3.15 | 3.05 |  |  |  |
| E2                   | 1.60 | 2.00 | 1.80 |  |  |  |
| E3                   | 0.95 | 1.35 | 1.15 |  |  |  |
| E4                   | 0.10 | 0.30 | 0.20 |  |  |  |
| е                    | -    | -    | 0.65 |  |  |  |
| k                    | 0.50 | 0.90 | 0.70 |  |  |  |
| L                    | 0.30 | 0.50 | 0.40 |  |  |  |
| θ                    | 0°   | 12°  | 10°  |  |  |  |
| All Dimensions in mm |      |      |      |  |  |  |

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8 (SWP) (Type UX)



| Dimensions | Value (in mm) |
|------------|---------------|
| С          | 0.650         |
| Х          | 0.420         |
| X1         | 0.420         |
| X2         | 0.230         |
| Х3         | 2.600         |
| X4         | 3.500         |
| Υ          | 0.700         |
| Y1         | 0.550         |
| Y2         | 1.650         |
| Y3         | 0.600         |
| Y4         | 2.450         |
| Y5         | 0.400         |
| Y6         | 3.700         |

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.



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